

MA174

Silicon planer type

For small power rectification and surge absorption

■ Features

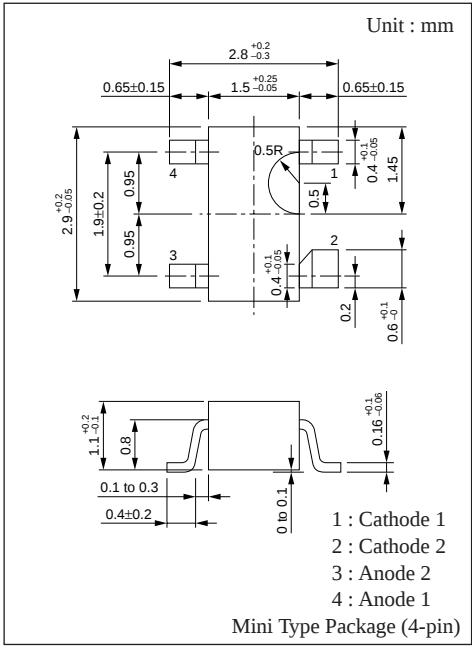
- Independent incorporating of two elements, enabling high-density mounting
- High voltage resistance (V_R : 200V), enabling rectification

■ Absolute Maximum Ratings ($T_a= 25^{\circ}\text{C}$)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	200	V
Repetitive peak reverse voltage	V_{RRM}	250	V
Non-repetitive peak reverse surge voltage	V_{RSM}	300	V
Output current	I_O	⊛ 100	mA
Repetitive peak forward current	I_{FRM}	⊛ 225	mA
Non-repetitive peak forward surge current	$I_{FSM} *$	⊛ 500	mA
Junction temperature	T_j	125	$^{\circ}\text{C}$
Storage temperature	T_{stg}	- 55 to +125	$^{\circ}\text{C}$

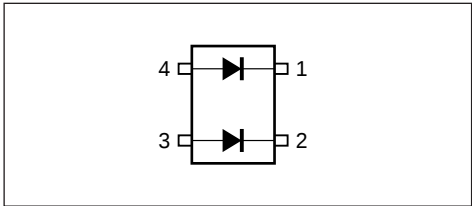
⊛ Value in single diode used

* $t=1\text{s}$



Marking Symbol : M2Q

■ Internal Connection



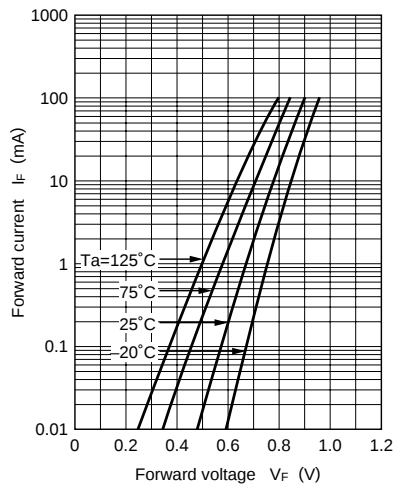
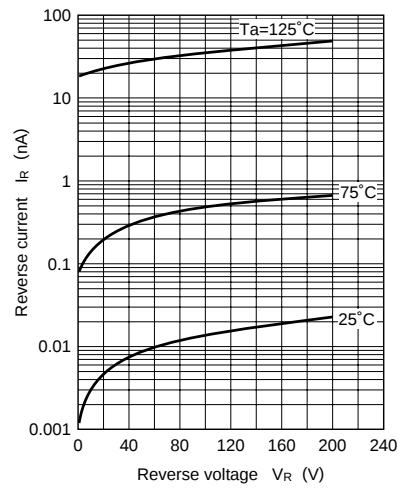
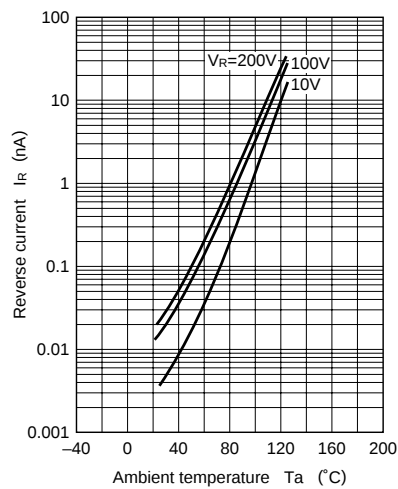
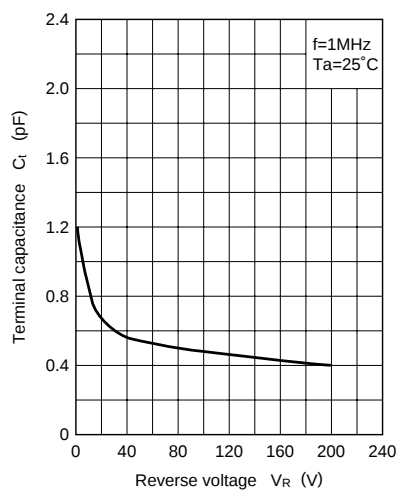
■ Electrical Characteristics ($T_a= 25^{\circ}\text{C}$)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R= 200\text{V}$			1.0	μA
Forward voltage (DC)	V_F	$I_F=100\text{mA}$			1.3	V

❖ Rated input/output frequency : 3MHz

■ Marking



$I_F - V_F$  $I_R - V_R$  $V_F - T_a$ $I_R - T_a$  $C_t - V_R$  $I_F(\text{surge}) - t_w$ 